Erratum to: Effects of in situ annealing on the properties of Al-doped ZnO thin films deposited by RF magnetron sputtering

Deok-Kyu Kim · Choon-Bae Park

Published online: 19 February 2014
© Springer Science+Business Media New York 2014

Erratum to: J Mater Sci: Mater Electron
DOI 10.1007/s10854-013-1694-0

The Acknowledgement was inadvertently omitted from the original publication of this article. The text should read as given below.

Acknowledgments This paper was supported by Wonkwang University in 2013.

The online version of the original article can be found under doi:[10.1007/s10854-013-1694-0](https://doi.org/10.1007/s10854-013-1694-0).

D.-K. Kim
Advanced Development Team, Samsung Electronics Co. Ltd.,
Yongin 446-711, Gyeonggi, Korea

C.-B. Park (✉)
Division of Electrical, Information and Communication
Engineering, Wonkwang University, Iksan 570-749, Jeonbuk,
Korea
e-mail: cbpark@wonkwang.ac.kr